

IRFP048PbF

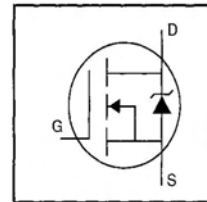
- Dynamic dv/dt Rating
- Isolated Central Mounting Hole
- 175°C Operating Temperature
- Ease of Paralleling
- Simple Drive Requirements

• Lead-Free

Description

Third Generation HEXFETs from International Rectifier provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

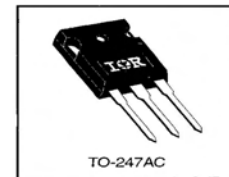
The TO-247 package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220 devices. The TO-247 is similar but superior to the earlier TO-218 package because of its isolated mounting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.



$$V_{DSS} = 60V$$

$$R_{DS(on)} = 0.018\Omega$$

$$I_D = 70^*A$$



Absolute Maximum Ratings

	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	70*	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 10 V$	52	
I_{DM}	Pulsed Drain Current ①	290	
$P_D @ T_C = 25^\circ C$	Power Dissipation	190	W
	Linear Derating Factor	1.3	W/°C
V_{GS}	Gate-to-Source Voltage	± 20	V
E_{AS}	Single Pulse Avalanche Energy ②	200	mJ
dv/dt	Peak Diode Recovery dv/dt ③	4.5	V/ns
T_J T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	°C
	Soldering Temperature, for 10 seconds	300 (1.6mm from case)	
	Mounting Torque, 6-32 or M3 screw	10 lbf•in (1.1 N•m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	—	0.80	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient	—	—	40	

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	60	—	—	V	V _{GS} =0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.060	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.018	Ω	V _{GS} =10V, I _D =44A ③
V _{GS(th)}	Gate Threshold Voltage	2.0	—	4.0	V	V _{DS} =V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	20	—	—	S	V _{DS} =25V, I _D =44A ③
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} =60V, V _{GS} =0V
		—	—	250		V _{DS} =48V, V _{GS} =0V, T _J =150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} =20V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} =-20V
Q _g	Total Gate Charge	—	—	110	nC	I _D =72A
Q _{gs}	Gate-to-Source Charge	—	—	29		V _{DS} =48V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	—	38		V _{GS} =10V See Fig. 6 and 13 ④
t _{d(on)}	Turn-On Delay Time	—	8.1	—	ns	V _{DD} =30V
t _r	Rise Time	—	250	—		I _D =72A
t _{d(off)}	Turn-Off Delay Time	—	210	—		R _G =9.1Ω
t _f	Fall Time	—	250	—		R _D =0.34Ω See Figure 10 ④
L _D	Internal Drain Inductance	—	5.0	—	nH	Between lead, 6 mm (0.25in.) from package and center of die contact
L _S	Internal Source Inductance	—	13	—		
C _{iss}	Input Capacitance	—	2400	—	pF	V _{GS} =0V
C _{oss}	Output Capacitance	—	1300	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	190	—		f=1.0MHz See Figure 5

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	70*	A	MOSFET symbol showing the integral reverse p-n junction diode.
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	290		
V _{SD}	Diode Forward Voltage	—	—	2.0	V	T _J =25°C, I _S =73A, V _{GS} =0V ④
t _{rr}	Reverse Recovery Time	—	120	180	ns	T _J =25°C, I _F =72A
Q _{rr}	Reverse Recovery Charge	—	0.50	0.80	μC	di/dt=100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by L _S +L _D)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature (See Figure 11)
- ② V_{DD}=25V, starting T_J=25°C, L=43μH, R_G=25Ω, I_{AS}=73A (See Figure 12)
- ③ I_{SD}≤72A, di/dt≤200A/μs, V_{DD}≤V_{(BR)DSS}, T_J≤175°C
- ④ Pulse width ≤ 300 μs; duty cycle ≤2%.
- * Current limited by the package, (Die Current =73A)

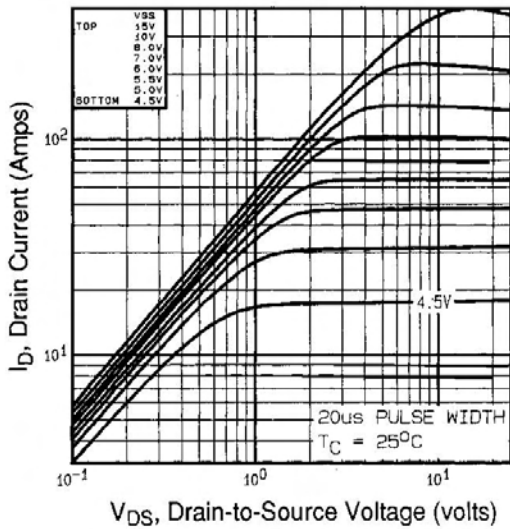


Fig 1. Typical Output Characteristics,
 $T_C=25^\circ\text{C}$

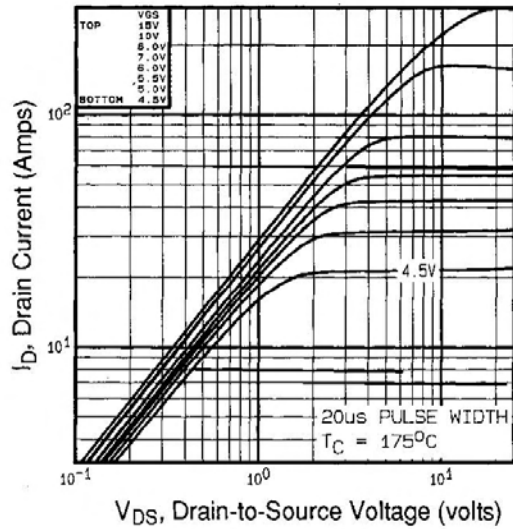


Fig 2. Typical Output Characteristics,
 $T_C=175^\circ\text{C}$

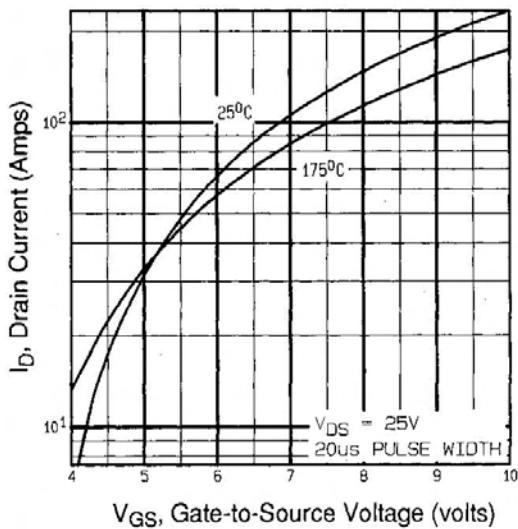


Fig 3. Typical Transfer Characteristics

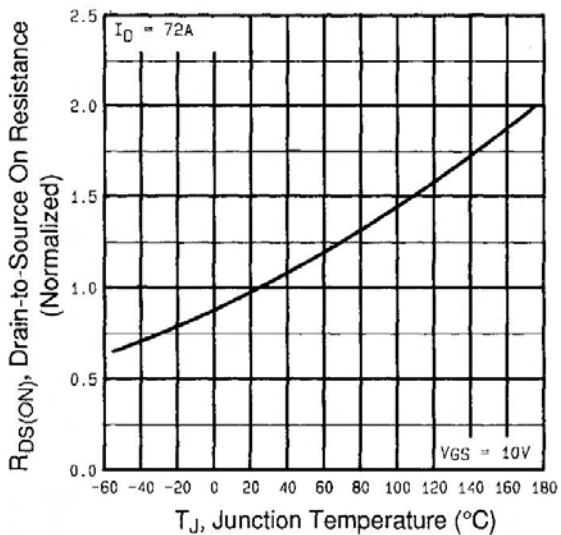


Fig 4. Normalized On-Resistance
 Vs. Temperature

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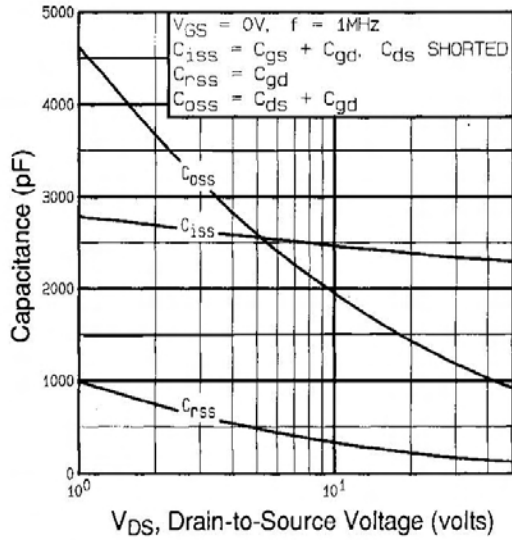


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

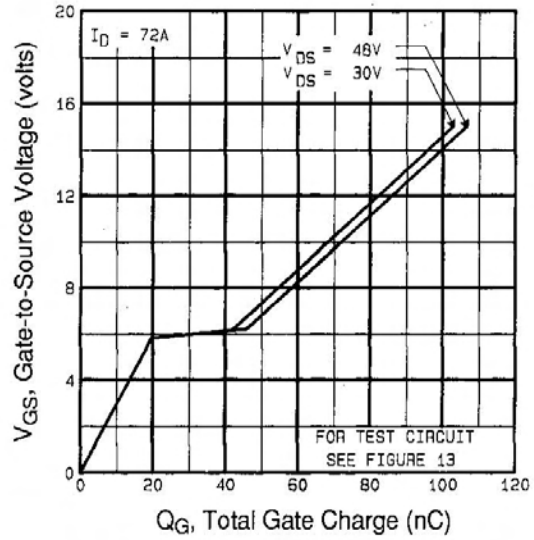


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

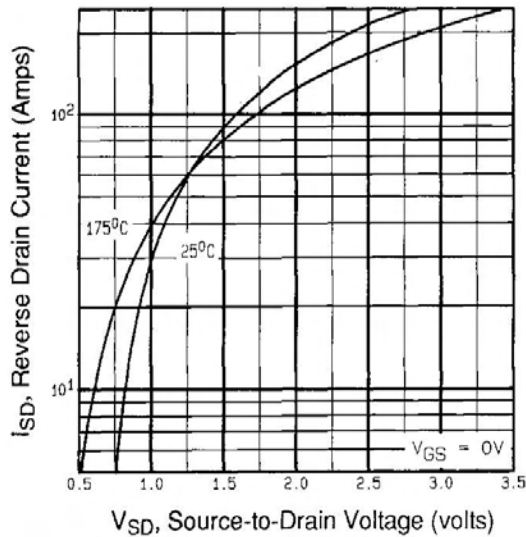


Fig 7. Typical Source-Drain Diode Forward Voltage

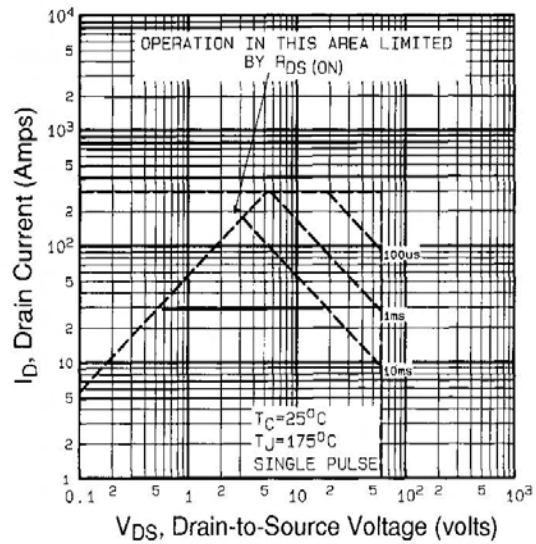


Fig 8. Maximum Safe Operating Area

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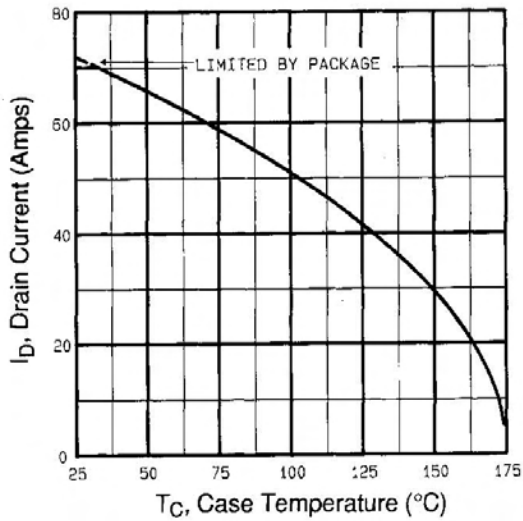


Fig 9. Maximum Drain Current Vs. Case Temperature

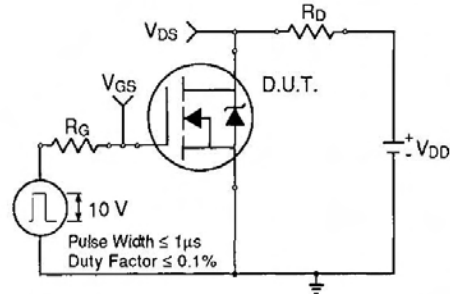


Fig 10a. Switching Time Test Circuit

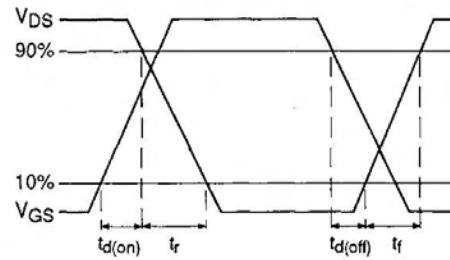


Fig 10b. Switching Time Waveforms

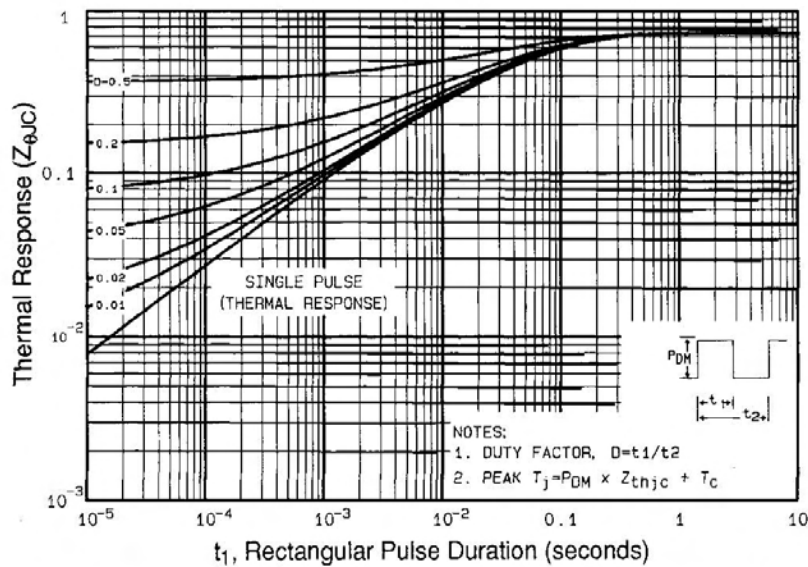


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

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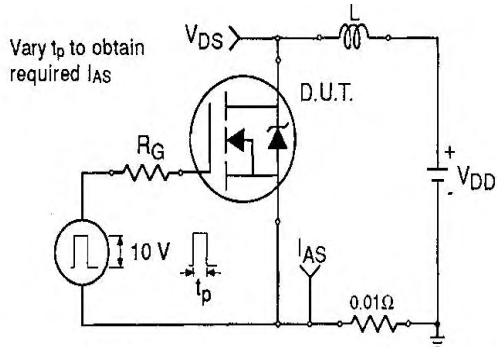


Fig 12a. Unclamped Inductive Test Circuit

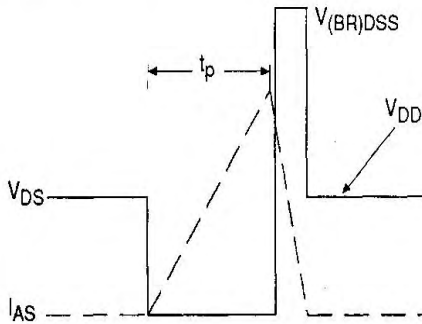


Fig 12b. Unclamped Inductive Waveforms

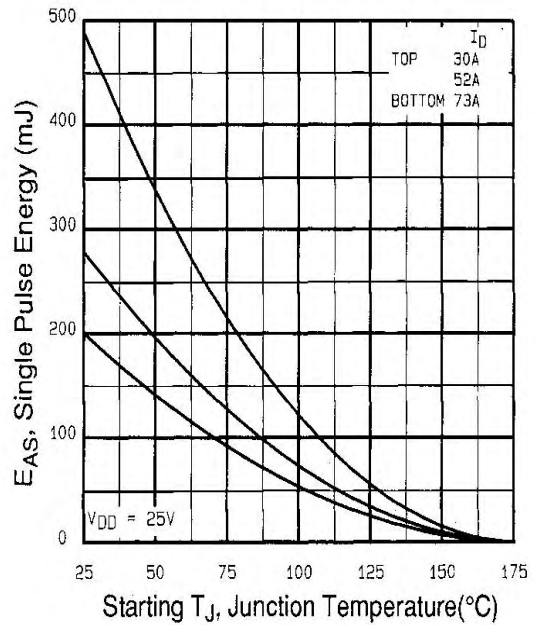


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

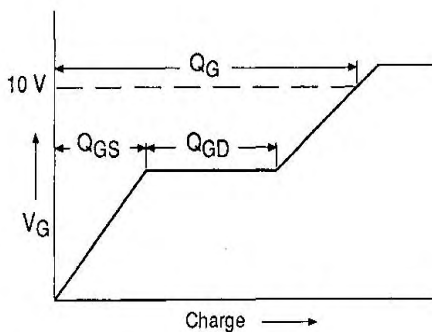


Fig 13a. Basic Gate Charge Waveform

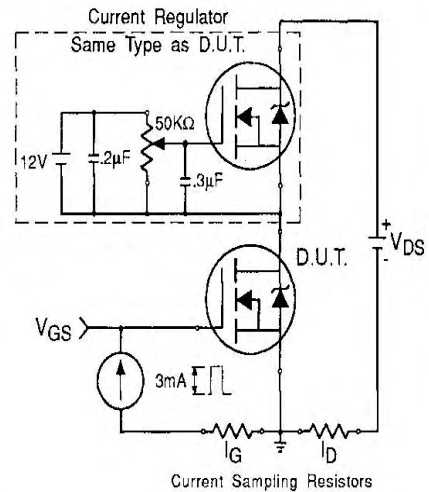
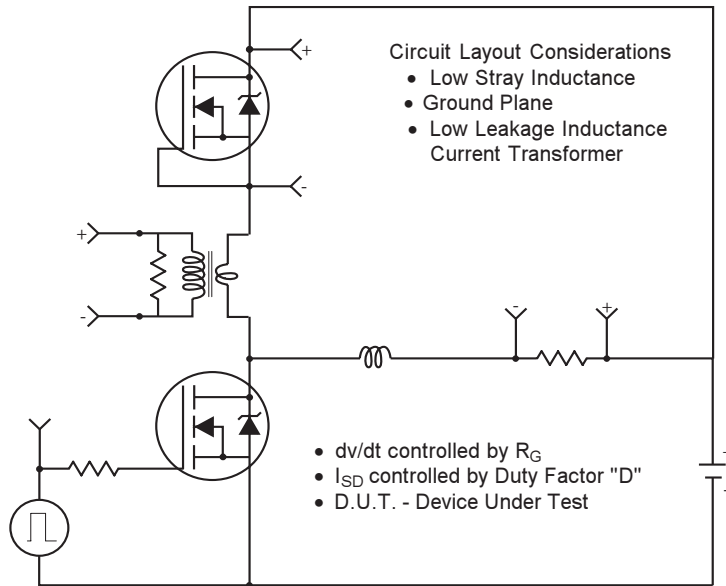


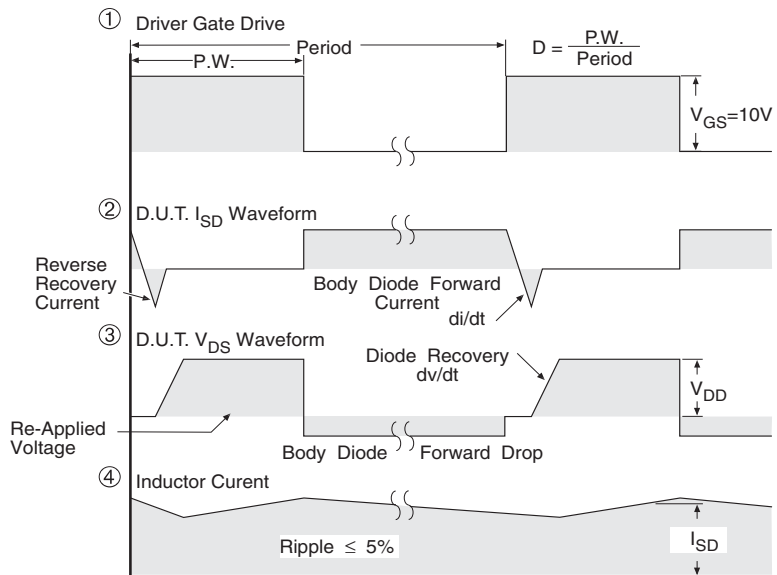
Fig 13b. Gate Charge Test Circuit

Peak Diode Recovery dv/dt Test Circuit



* Reverse Polarity for P-Channel

** Use P-Channel Driver for P-Channel Measurements



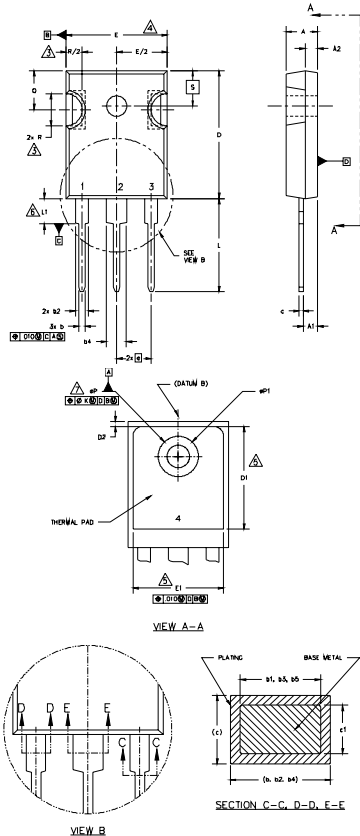
*** $V_{GS} = 5.0V$ for Logic Level and 3V Drive Devices

Fig -14 For N Channel HEXFETS

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TO-247AC Package Outline Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154" [3.91].
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247 WITH THE EXCEPTION OF DIMENSION c.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.37	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.034	0.38	0.86	
c1	.015	.030	0.38	0.76	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.030	0.51	0.76	
E	.602	.625	15.29	15.87	4
E1	.540	-	13.72	-	
e	.215 BSC		5.46 BSC		
Øk	.010		2.54		
L	.559	.634	14.20	16.10	
L1	.146	.169	3.71	4.29	
N	3		7.62 BSC		
ØP	.140	.144	3.56	3.66	
ØP1	-	.275	-	6.98	
Q	.209	.224	5.31	5.69	
R	.178	.216	4.52	5.49	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

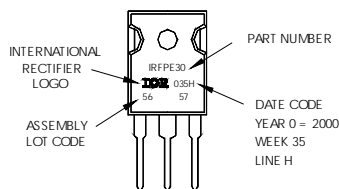
- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AC Part Marking Information

EXAMPLE: THIS IS AN IRFPE30 WITH ASSEMBLY LOT CODE 5657 ASSEMBLED ON WW 35, 2000 IN THE ASSEMBLY LINE "H"
Note: "P" in assembly line position indicates "Lead-Free"



Data and specifications subject to change without notice.



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